



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

**SURFACE MOUNT
NPN Digital Silicon Transistor**

VOLTAGE 50 Volts CURRENT 100 mAmpere

CHDTC114TEPT

APPLICATION

- * Switching circuit, Inverter, Interface circuit, Driver circuit.

FEATURE

- * Small surface mounting type. (SC-75/SOT-416)
- * High current gain.
- * Suitable for high packing density.
- * Low collector-emitter saturation.
- * High saturation current capability.
- * Internal isolated NPN transistors in one package.
- * Built in single resistor($R_1=10\text{k}\Omega$, Typ.)

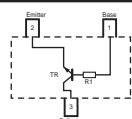
CONSTRUCTION

- * One NPN transistors and bias of thin-film resistors in one package.

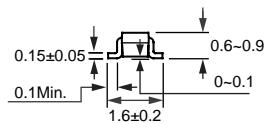
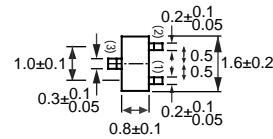
MARKING

TEB

CIRCUIT



SC-75/SOT-416



Dimensions in millimeters

SC-75/SOT-416

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-Base voltage		50	V
V_{CEO}	Collector-Emitter voltage		50	V
V_{EBO}	Emitter-Base voltage		5	V
$I_C(\text{Max.})$	Collector current		100	mA
P_D	Power dissipation	$T_{\text{amb}} \leq 25^\circ\text{C}$, Note 1	150	mW
T_{STG}	Storage temperature		-55 +150	°C
T_J	Junction temperature		-55 +150	°C
$R_{\theta J-S}$	Thermal resistance , Note 1	junction - soldering point	140	°C/W

Note

- Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC (CHDTC114TEPT)

CHARACTERISTICS

$T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BVCBO	Collector-base breakdown voltage	$I_c=50\mu\text{A}$	50	—	—	V
BVCEO	Collector-emitter breakdown voltage	$I_c=1.0\text{mA}$	50	—	—	V
BVEBO	Emitter-base breakdown voltage	$I_E=50\mu\text{A}$	5.0	—	—	V
ICBO	Collector cutoff current	$V_{CB}=50\text{V}$	—	—	0.5	μA
IEBO	Emitter cutoff current	$V_{EB}=4\text{V}$	—	—	0.5	μA
VCE(sat)	Collector-emitter saturation voltage	$I_c/I_b=10\text{mA}/1\text{mA}$	—	—	0.3	V
hFE	DC current gain	$I_c=1\text{mA}; V_{CE}=5.0\text{V}$	100	300	600	
R ₁	Input resistor		7.0	10.0	13.0	K Ω
f _T	Transition frequency	$I_c=5\text{mA}, V_{CE}=10.0\text{V}$ $f=100\text{MHz}$	—	250	—	MHz

Note

1. Pulse test: $t_p \leq 300\mu\text{s}$; $\delta \leq 0.02$.

RATING CHARACTERISTIC CURVES (CHDTC114TEPT)

Typical Electrical Characteristics

Fig.1 DC current gain vs. collector current

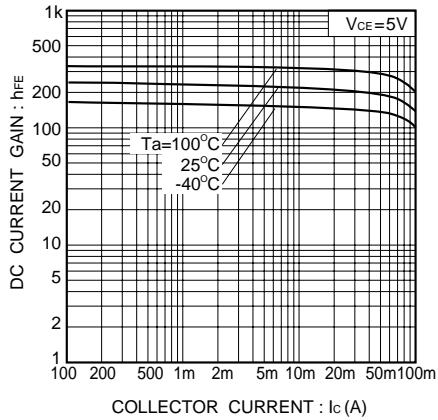


Fig.2 Collector-emitter voltage vs. collector current

